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(71) Applicant *(for all designated States except US)*: **APPLIED MATERIALS, INC.** [US/US]; 3050 Bowers Avenue, Santa Clara, CA 95054 (US).

(72) Inventors; and
(75) Inventors/Applicants *(for US only)*: **LIANG, Jingmei** [CN/US]; 1256 Mountain Quail Circle, San Jose, CA 95120 (US). **CHEN, Xiaolin** [CA/US]; 3263 Sleeping Meadow Way, San Ramon, CA 94582 (US). **MILLER, Matthew, L.** [US/US]; 38419 Ajuga Court, Newark, CA 94560 (US). **INGLE, Nitin, K.** [US/US]; 1435 Graywood Drive, San Jose, CA 95129 (US). **VENKATARAMAN, Shankar** [US/US]; 5974 Thorntree Drive, San Jose, CA 95120 (US).

(74) Agents: **BERNARD, Eugene, J.** et al.; Townsend and Townsend and Crew LLP, 1400 Wewatta Street, Suite 600, Denver, CO 80202 (US).

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(54) Title: DIELECTRIC FILM GROWTH WITH RADICALS PRODUCED USING FLEXIBLE NITROGEN/HYDROGEN RATIO

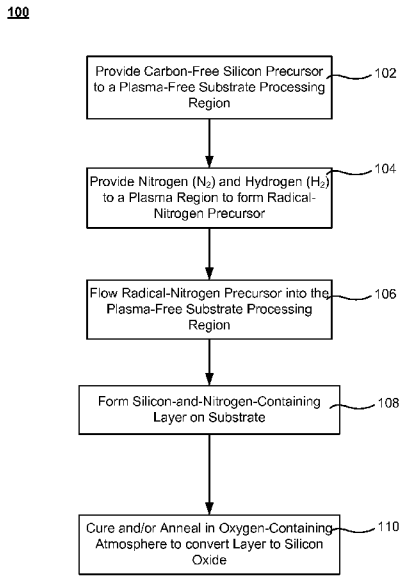


FIG. 1

(57) Abstract: Methods of forming dielectric layers are described. The method may include the steps of mixing a silicon-containing precursor with a radical-nitrogen precursor, and depositing a dielectric layer on a substrate. The radical-nitrogen precursor is formed in a remote plasma by flowing hydrogen (H2) and nitrogen (N2) into the plasma in order to allow adjustment of the nitrogen/hydrogen ratio. The dielectric layer is initially a silicon-and-nitrogen-containing layer which may be converted to a silicon-and-oxygen-containing layer by curing and/or annealing the film in an oxygen-containing environment.

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